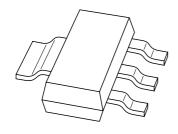
### **DISCRETE SEMICONDUCTORS**

# DATA SHEET



## BSP60; BSP61; BSP62 PNP Darlington transistors

Product data sheet Supersedes data of 1999 Apr 29 2001 May 31



### **PNP Darlington transistors**

**BSP60**; **BSP61**; **BSP62** 

#### **FEATURES**

- High current (max. 0.5 A)
- Low voltage (max. 80 V)
- Integrated diode and resistor.

#### **APPLICATIONS**

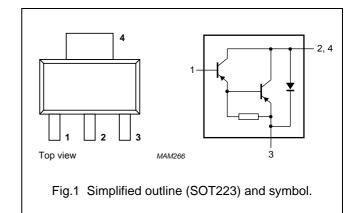
- Industrial switching applications such as:
  - Print hammer
  - Solenoid
  - Relay and lamp drivers.

#### **DESCRIPTION**

PNP Darlington transistor in a SOT223 plastic package. NPN complements: BSP50, BSP51 and BSP52.

#### **PINNING**

| PIN  | DESCRIPTION |  |
|------|-------------|--|
| 1    | base        |  |
| 2, 4 | collector   |  |
| 3    | emitter     |  |



#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL           | PARAMETER                     | CONDITIONS                       | MIN. | MAX. | UNIT |
|------------------|-------------------------------|----------------------------------|------|------|------|
| V <sub>CBO</sub> | collector-base voltage        | open emitter                     |      |      |      |
|                  | BSP60                         |                                  | _    | -60  | V    |
|                  | BSP61                         |                                  | _    | -80  | V    |
|                  | BSP62                         |                                  | _    | -90  | V    |
| V <sub>CES</sub> | collector-emitter voltage     | $V_{BE} = 0$                     |      |      |      |
|                  | BSP60                         |                                  | _    | -45  | V    |
|                  | BSP61                         |                                  | _    | -60  | V    |
|                  | BSP62                         |                                  | _    | -80  | V    |
| V <sub>EBO</sub> | emitter-base voltage          | open collector                   | _    | -5   | V    |
| I <sub>C</sub>   | collector current (DC)        |                                  | _    | -1   | А    |
| I <sub>CM</sub>  | peak collector current        |                                  | _    | -2   | Α    |
| I <sub>B</sub>   | base current (DC)             |                                  | _    | -100 | mA   |
| P <sub>tot</sub> | total power dissipation       | T <sub>amb</sub> ≤ 25 °C; note 1 | _    | 1.25 | W    |
| T <sub>stg</sub> | storage temperature           |                                  | -65  | +150 | °C   |
| Tj               | junction temperature          |                                  | _    | 150  | °C   |
| T <sub>amb</sub> | operating ambient temperature |                                  | -65  | +150 | °C   |

#### Note

 Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>.
 For other mounting conditions, see "Thermal considerations for the SOT223 in the General Part of associated Handbook".

2001 May 31 2

### PNP Darlington transistors

BSP60; BSP61; BSP62

#### THERMAL CHARACTERISTICS

| SYMBOL              | PARAMETER                                        | CONDITIONS | VALUE | UNIT |
|---------------------|--------------------------------------------------|------------|-------|------|
| R <sub>th j-a</sub> | thermal resistance from junction to ambient      | note 1     | 98    | K/W  |
| R <sub>th j-s</sub> | thermal resistance from junction to solder point |            | 17    | K/W  |

#### Note

1. Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>. For other mounting conditions, see *"Thermal considerations for the SOT223 in the General Part of associated Handbook"*.

#### **CHARACTERISTICS**

 $T_i = 25$  °C unless otherwise specified.

| SYMBOL                                                  | PARAMETER                       | CONDITIONS                                                                | MIN. | TYP. | MAX. | UNIT |
|---------------------------------------------------------|---------------------------------|---------------------------------------------------------------------------|------|------|------|------|
| I <sub>CES</sub>                                        | collector cut-off current       |                                                                           |      |      |      |      |
|                                                         | BSP60                           | $V_{BE} = 0; V_{CE} = -45 \text{ V}$                                      | _    | _    | -50  | nA   |
|                                                         | BSP61                           | $V_{BE} = 0; V_{CE} = -60 \text{ V}$                                      | _    | _    | -50  | nA   |
|                                                         | BSP62                           | $V_{BE} = 0; V_{CE} = -80 \text{ V}$                                      | _    | _    | -50  | nA   |
| I <sub>EBO</sub>                                        | emitter cut-off current         | I <sub>C</sub> = 0; V <sub>EB</sub> = -4 V                                | -    | _    | -50  | nA   |
| h <sub>FE</sub>                                         | DC current gain                 | $V_{CE} = -10 \text{ V}$ ; note 1; see Fig.2                              |      |      |      |      |
|                                                         |                                 | $I_{\rm C} = -150 \; {\rm mA}$                                            | 1000 | _    | _    |      |
|                                                         |                                 | $I_{\rm C} = -500 \; {\rm mA}$                                            | 2000 | _    | _    |      |
| V <sub>CEsat</sub>                                      | collector-emitter saturation    | $I_C = -500 \text{ mA}; I_B = -0.5 \text{ mA}$                            | -    | _    | -1.3 | V    |
| voltage                                                 |                                 | $I_C = -500 \text{ mA}; I_B = -0.5 \text{ mA};$<br>$T_j = 150 \text{ °C}$ | _    | _    | -1.3 | V    |
| V <sub>BEsat</sub>                                      | base-emitter saturation voltage | $I_C = -500 \text{ mA}; I_B = -0.5 \text{ mA}$                            | -    | _    | -1.9 | V    |
| f <sub>T</sub>                                          | transition frequency            | $I_C = -500 \text{ mA}; V_{CE} = -5 \text{ V};$<br>f = 100 MHz            | _    | 200  | _    | MHz  |
| Switching times (between 10% and 90% levels); see Fig.3 |                                 |                                                                           |      |      |      |      |
| t <sub>on</sub>                                         | turn-on time                    | $I_{Con} = -500 \text{ mA}; I_{Bon} = -0.5 \text{ mA};$                   | _    | 400  | _    | ns   |
| t <sub>off</sub>                                        | turn-off time                   | I <sub>Boff</sub> = 0.5 mA                                                | _    | 1500 | _    | ns   |

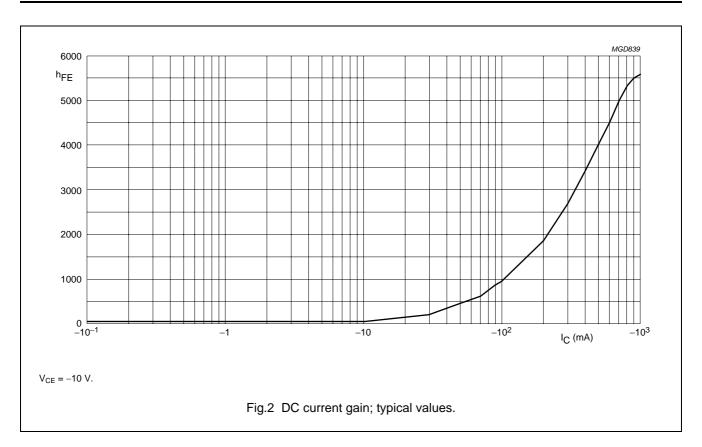
#### Note

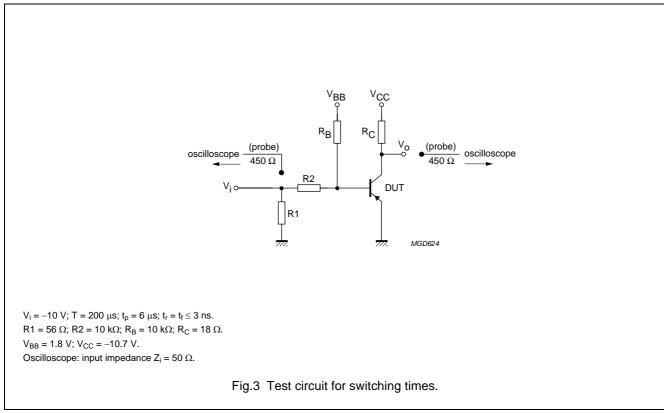
1. Pulse test:  $t_p \leq 300~\mu s;~\delta \leq 0.02.$ 

2001 May 31 3

### PNP Darlington transistors

### BSP60; BSP61; BSP62





2001 May 31 4

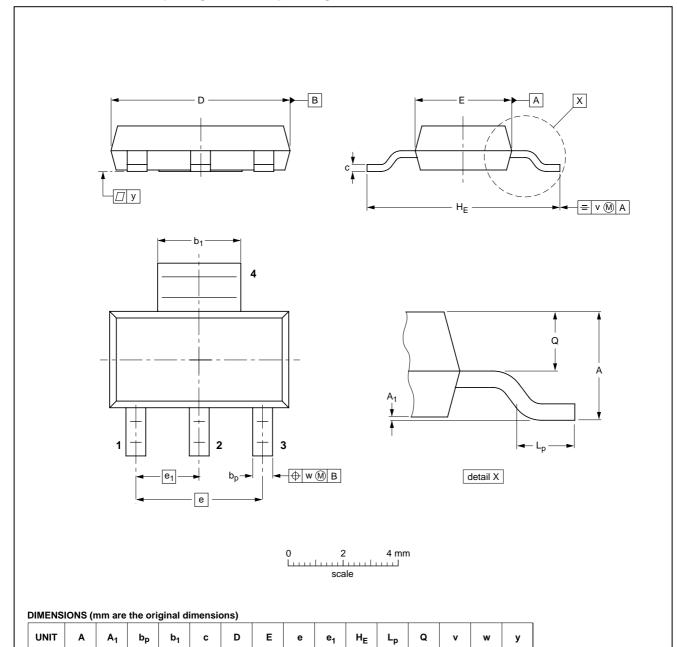
### PNP Darlington transistors

BSP60; BSP61; BSP62

#### **PACKAGE OUTLINE**

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

**SOT223** 



| OUTLINE |     | REFERENCES |       |  | EUROPEAN   | ISSUE DATE                       |
|---------|-----|------------|-------|--|------------|----------------------------------|
| VERSION | IEC | JEDEC      | EIAJ  |  | PROJECTION | ISSUL DATE                       |
| SOT223  |     |            | SC-73 |  |            | <del>-97-02-28</del><br>99-09-13 |

7.3

1.1

0.95

0.85

0.1

0.1

2001 May 31 5

0.80

0.60

0.10

0.01

1.8

mm

3.1 2.9 6.7

3.7

3.3

0.32

0.22

### PNP Darlington transistors

BSP60; BSP61; BSP62

#### **DATA SHEET STATUS**

| DOCUMENT<br>STATUS <sup>(1)</sup> | PRODUCT<br>STATUS <sup>(2)</sup> | DEFINITION                                                                            |
|-----------------------------------|----------------------------------|---------------------------------------------------------------------------------------|
| Objective data sheet              | Development                      | This document contains data from the objective specification for product development. |
| Preliminary data sheet            | Qualification                    | This document contains data from the preliminary specification.                       |
| Product data sheet                | Production                       | This document contains the product specification.                                     |

#### **Notes**

- 1. Please consult the most recently issued document before initiating or completing a design.
- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

6

#### **DISCLAIMERS**

**General** — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions

above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

**Export control** — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

**Quick reference data** — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

### **NXP Semiconductors**

#### **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors. No changes were made to the content, except for the legal definitions and disclaimers.

#### **Contact information**

For additional information please visit: http://www.nxp.com

For sales offices addresses send e-mail to: salesaddresses@nxp.com

© NXP B.V. 2009

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Printed in The Netherlands 613514/05/pp7 Date of release: 2001 May 31 Document order number: 9397 750 07906



### **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Darlington Transistors category:

Click to view products by NXP manufacturer:

Other Similar products are found below:

281287X SMMBT6427LT1G 2N7371 BDV64B JANTXV2N6287 028710A SMMBTA64LT1G 2N6350 2SB1214-TL-E

SMMBTA14LT1G SBSP52T1G NJVMJD117T4G Jantx2N6058 2N6353 LB1205-L-E 500-00005 2N6053 NJVMJD112G Jan2N6350

Jantx2N6352 Jantx2N6350 BULN2803LVS ULN2001N 2SB1383 2SB1560 2SB852KT146B TIP112TU TIP122TU BCV27 MMBTA13
TP MMBTA14-TP MMSTA28T146 BSP50H6327XTSA1 KSH122TF NTE2557 NJVNJD35N04T4G TIP115 MPSA29-D26Z MJD127T4

FJB102TM BCV26E6327HTSA1 BCV46E6327HTSA1 BCV47E6327HTSA1 BSP61H6327XTSA1 BU941ZPFI 2SB1316TL 2SD1980TL

NTE2350 NTE245 NTE246